

# 2SK3505-01MR

FUJI POWER MOSFET

## Super FAP-G Series

## N-CHANNEL SILICON POWER MOSFET

### Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

### Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

### Maximum ratings and characteristic Absolute maximum ratings

( $T_c=25^\circ\text{C}$  unless otherwise specified)

Item	Symbol	Ratings	Unit	
Drain-source voltage	$V_{DS}$	500	V	
Continuous drain current	$I_D$	$\pm 14$	A	
Pulsed drain current	$I_{D(puls)}$	$\pm 56$	A	
Gate-source voltage	$V_{GS}$	$\pm 30$	V	
Repetitive or non-repetitive	$I_{AR}^*2$	14	A	
Maximum Avalanche Energy	$E_{AS}^*1$	242	mJ	
Maximum Drain-Source $dV/dt$	$dV_{DS}/dt^*4$	20	kV/ $\mu\text{s}$	
Peak Diode Recovery $dV/dt$	$dV/dt^*3$	5	kV/ $\mu\text{s}$	
Max. power dissipation	$P_D$	$T_a=25^\circ\text{C}$	2.1	W
		$T_c=25^\circ\text{C}$	60	
Operating and storage temperature range	$T_{ch}$	+150	$^\circ\text{C}$	
	$T_{stg}$	-55 to +150	$^\circ\text{C}$	

\*1  $L=2.27\text{mH}$ ,  $V_{CC}=50\text{V}$  \*2  $T_{ch}\leq 150^\circ\text{C}$  \*3  $I_F\leq -I_D$ ,  $-di/dt=50\text{A}/\mu\text{s}$ ,  $V_{CC}\leq BV_{DS}$ ,  $T_{ch}\leq 150^\circ\text{C}$   
 \*4  $V_{DS}\leq 500\text{V}$

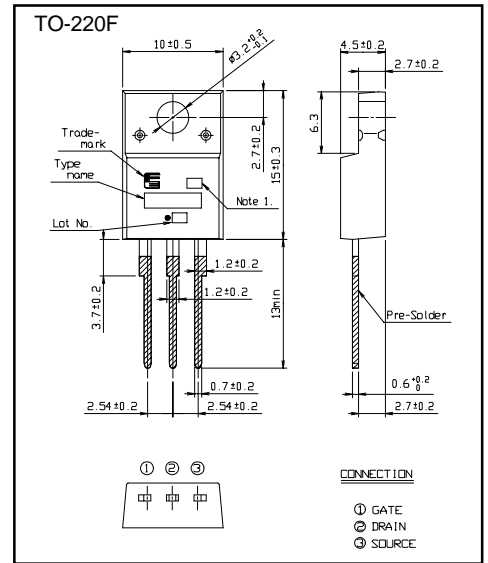
### Electrical characteristics ( $T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D=250\mu\text{A}$ $V_{GS}=0\text{V}$	500			V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$ $V_{DS}=V_{GS}$	3.0		5.0	V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=500\text{V}$ $V_{GS}=0\text{V}$			25	$\mu\text{A}$
		$V_{DS}=400\text{V}$ $V_{GS}=0\text{V}$			250	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=\pm 30\text{V}$ $V_{DS}=0\text{V}$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=7\text{A}$ $V_{GS}=10\text{V}$		0.35	0.46	$\Omega$
Forward transconductance	$g_{fs}$	$I_D=7\text{A}$ $V_{DS}=25\text{V}$	7	14		S
Input capacitance	$C_{iss}$	$V_{DS}=25\text{V}$		1600	2400	pF
Output capacitance	$C_{oss}$	$V_{GS}=0\text{V}$		160	240	
Reverse transfer capacitance	$C_{rss}$	$f=1\text{MHz}$		7	10.5	
Turn-on time $t_{on}$	$t_{d(on)}$	$V_{CC}=300\text{V}$ $I_D=7\text{A}$		18	27	ns
	$t_r$	$V_{GS}=10\text{V}$		16	24	
Turn-off time $t_{off}$	$t_{d(off)}$	$R_{GS}=10\Omega$		35	50	
	$t_f$			8	15	
Total Gate Charge	$Q_G$	$V_{CC}=250\text{V}$		33	50	nC
Gate-Source Charge	$Q_{GS}$	$I_D=14\text{A}$		12.5	19	
Gate-Drain Charge	$Q_{GD}$	$V_{GS}=10\text{V}$		10.5	16	
Avalanche capability	$I_{AV}$	$L=2.27\text{mH}$ $T_{ch}=25^\circ\text{C}$	14			A
Diode forward on-voltage	$V_{SD}$	$I_F=14\text{A}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$		1.00	1.50	V
Reverse recovery time	$t_{rr}$	$I_F=14\text{A}$ $V_{GS}=0\text{V}$		0.65		$\mu\text{s}$
Reverse recovery charge	$Q_{rr}$	$-di/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$		6.0		$\mu\text{C}$

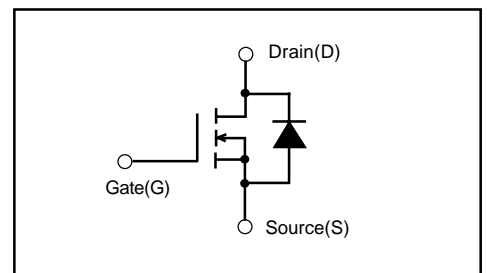
### Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			2.08	$^\circ\text{C}/\text{W}$
	$R_{th(ch-a)}$	channel to ambient			62.0	$^\circ\text{C}/\text{W}$

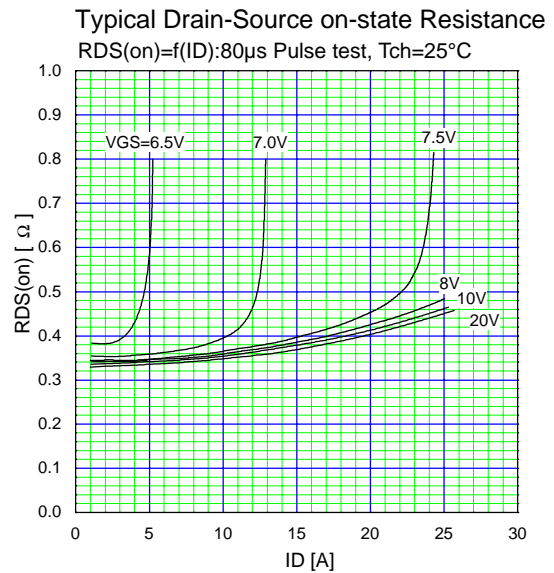
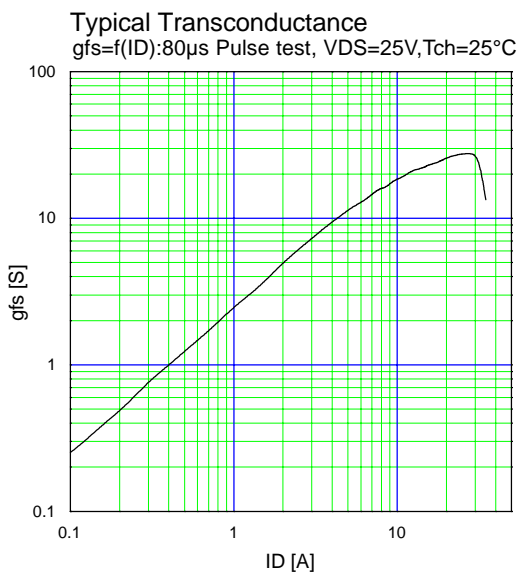
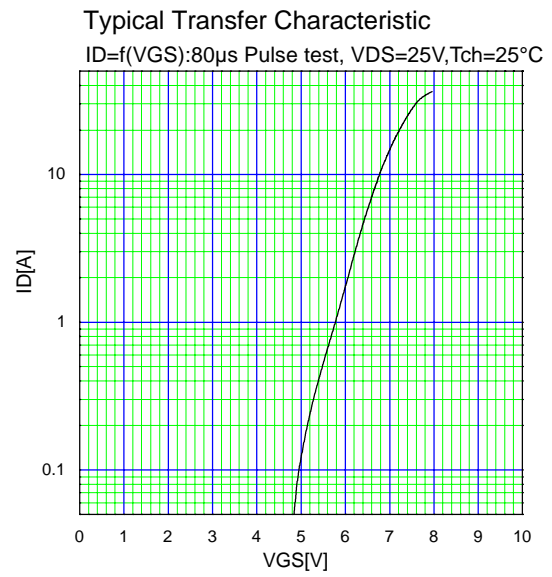
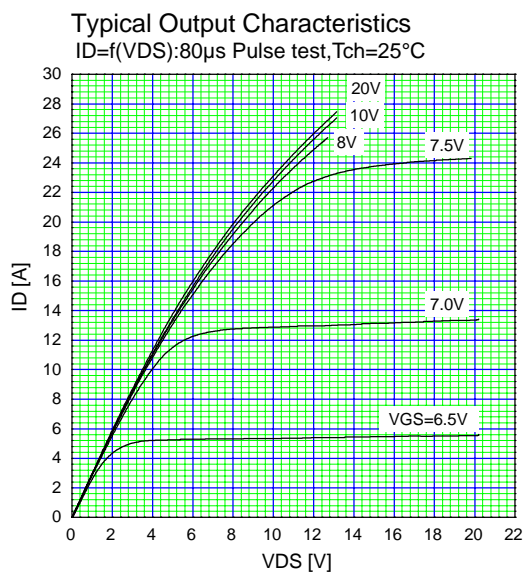
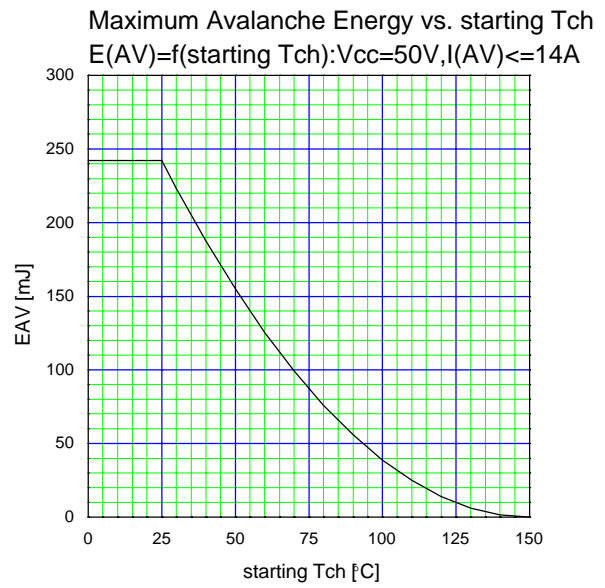
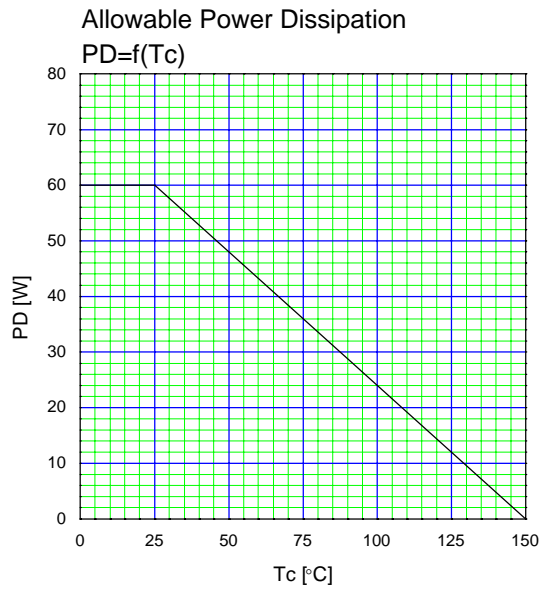
### Outline Drawings

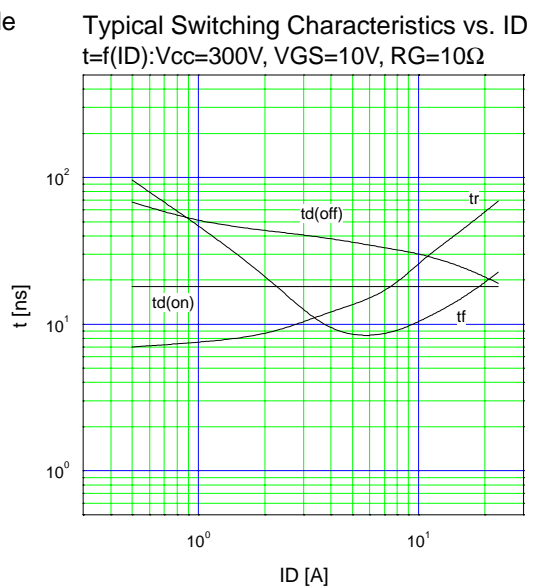
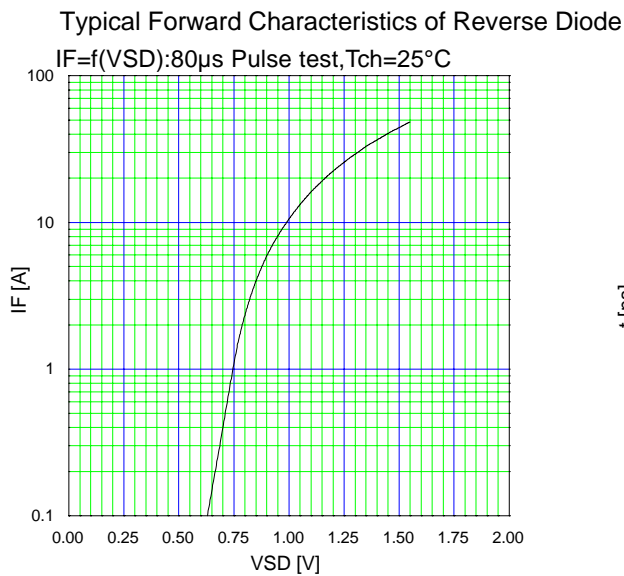
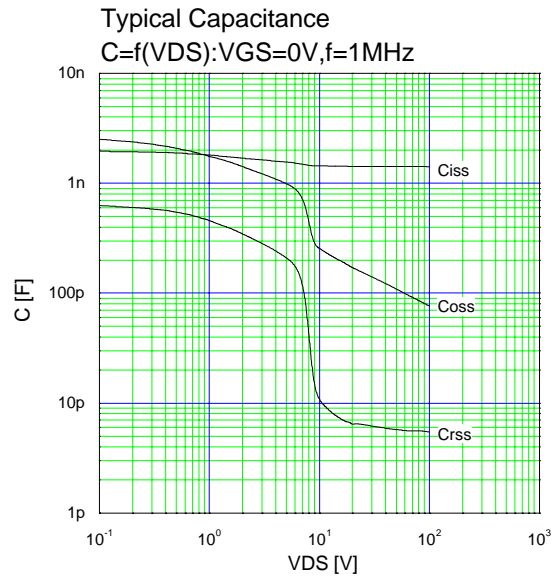
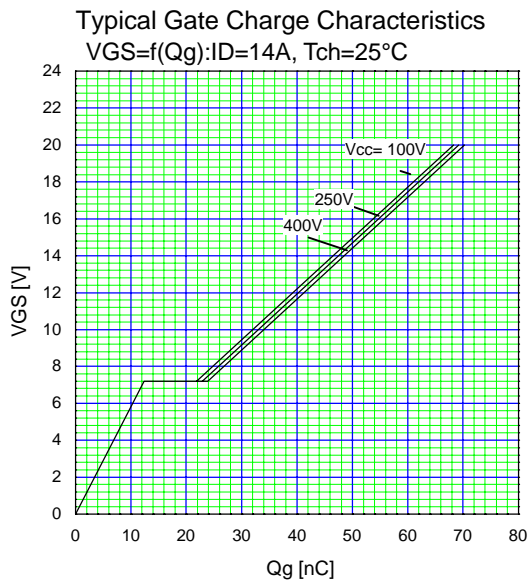
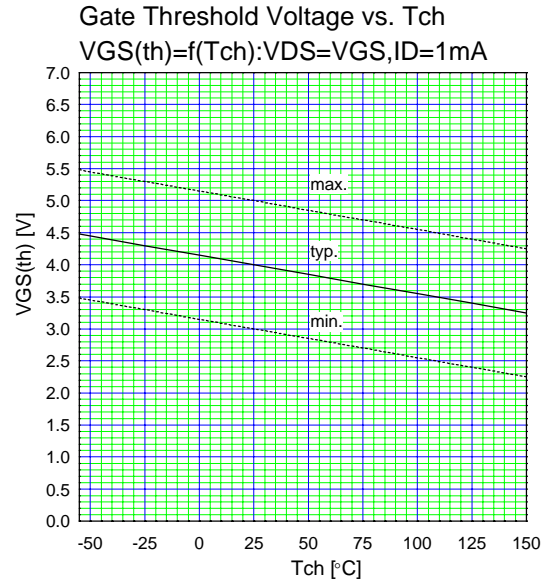
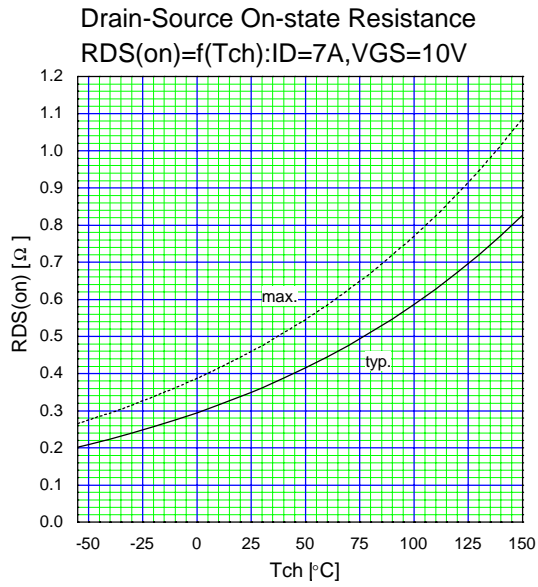


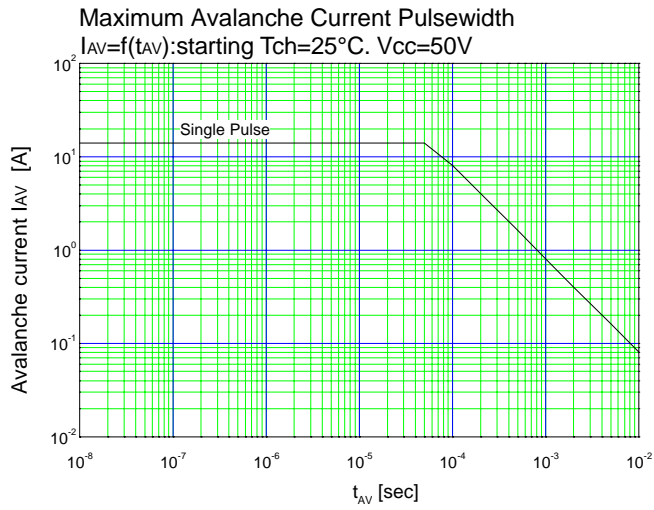
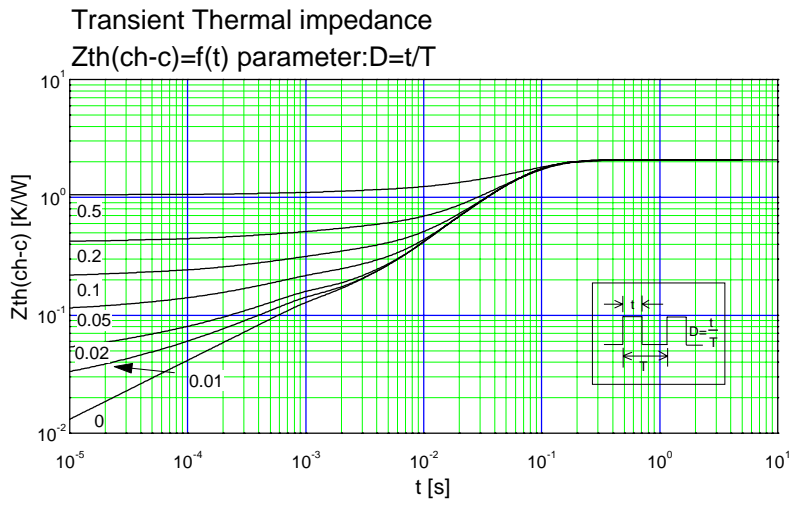
### Equivalent circuit schematic



■ Characteristics







This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.